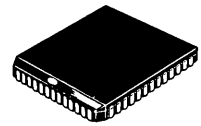
MCM67B618

Product Preview

64K x 18 Bit BurstRAM™ Synchronous Fast Static RAM

With Burst Counter and Self-Timed Write



FN PACKAGE
PLASTIC
CASE 778

The MCM67B618 is a 1,179,648 bit synchronous fast static random access memory designed to provide a burstable, high-performance, secondary cache for the i486 and Pentium™ microprocessors. It is organized as 65,536 words of 18 bits, fabricated with Motorola's high-performance silicon-gate BiCMOS technology. The device integrates input registers, a 2-bit counter, high speed SRAM, and high drive capability outputs onto a single monolithic circuit for reduced parts count implementation of cache data RAM applications. Synchronous design allows precise cycle control with the use of an external clock (K). BiCMOS circuitry reduces the overall power consumption of the integrated functions for greater reliability.

Addresses (A0 – A15), data inputs (D0 – D17), and all control signals except output enable ($\overline{G}$) are clock (K) controlled through positive-edge-triggered noninverting registers.

Bursts can be initiated with either address status processor ($\overline{ADSP}$) or address status cache controller ($\overline{ADSC}$) input pins. Subsequent burst addresses can be generated internally by the MCM67B618 (burst sequence imitates that of the i486 and Pentium) and controlled by the burst address advance ($\overline{ADV}$) input pin. The following pages provide more detailed information on burst controls.

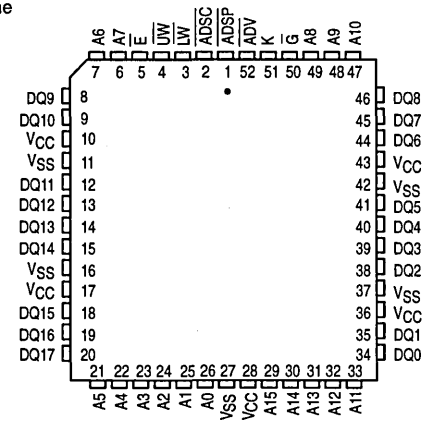
Write cycles are internally self-timed and are initiated by the rising edge of the clock (K) input. This feature eliminates complex off-chip write pulse generation and provides increased flexibility for incoming signals.

Dual write enables ($\overline{LW}$ and $\overline{UW}$) are provided to allow individually writeable bytes. $\overline{LW}$ controls DQ0 – DQ8 (the lower bits), while $\overline{UW}$ controls DQ9 – DQ17 (the upper bits).

This device is ideally suited for systems that require wide data bus widths and cache memory. See Figure 2 for applications information.

- Single 5 V ± 5% Power Supply
- Fast Access Times: 9/12/18 ns Max
- Byte Writeable via Dual Write Enables
- Internal Input Registers (Address, Data, Control)
- Internally Self-Timed Write Cycle
- $\overline{ADSP}$, $\overline{ADSC}$, and $\overline{ADV}$ Burst Control Pins
- Asynchronous Output Enable Controlled Three-State Outputs
- Common Data Inputs and Data Outputs
- 3.3 V I/O Compatible
- High Board Density 52-Lead PLCC Package

PIN ASSIGNMENT



PIN NAMES	
A0 – A15	Address Inputs
K	Clock
$\overline{ADV}$	Burst Address Advance
$\overline{LW}$	Lower Byte Write Enable
$\overline{UW}$	Upper Byte Write Enable
$\overline{ADSC}$	Controller Address Status
$\overline{ADSP}$	Processor Address Status
$\overline{E}$	Chip Enable
$\overline{G}$	Output Enable
DQ0 – DQ17	Data Input/Output
V_{CC}	+ 5 V Power Supply
V_{SS}	Ground

All power supply and ground pins must be connected for proper operation of the device.

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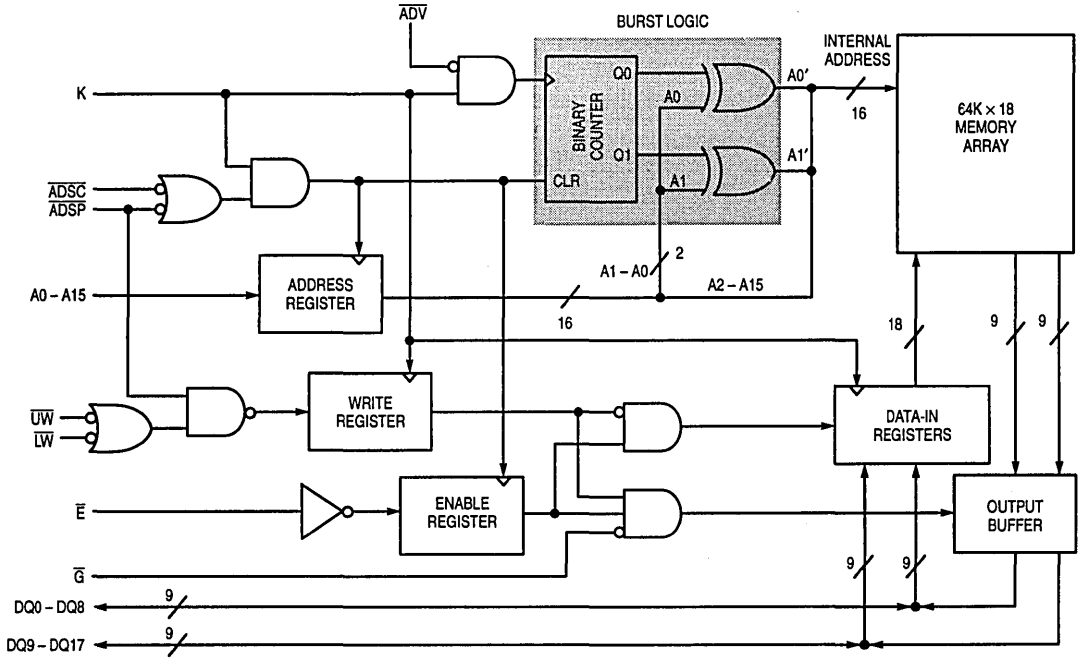
BLOCK DIAGRAM (See Note)



NOTE: All registers are positive-edge triggered. The $\overline{ADSC}$ or $\overline{ADSP}$ signals control the duration of the burst and the start of the next burst. When $\overline{ADSP}$ is sampled low, any ongoing burst is interrupted and a read (independent of $\overline{W}$ and $\overline{ADSC}$) is performed using the new external address. When $\overline{ADSC}$ is sampled low (and $\overline{ADSP}$ is sampled high), any ongoing burst is interrupted and a read or write (dependent on $\overline{W}$) is performed using the new external address. Chip enable ($\overline{E}$) is sampled only when a new base address is loaded. After the first cycle of the burst, $\overline{ADV}$ controls subsequent burst cycles. When $\overline{ADV}$ is sampled low, the internal address is advanced prior to the operation. When $\overline{ADV}$ is sampled high, the internal address is not advanced, thus inserting a wait state into the burst sequence accesses. Upon completion of a burst, the address will wrap around to its initial state. See **BURST SEQUENCE TABLE**. Write refers to either or both byte write enables ($\overline{LW}$, $\overline{UW}$).

BURST SEQUENCE TABLE (See Note)

External Address	A15 – A2	A1	A0
1st Burst Address	A15 – A2	A1	$\overline{A0}$
2nd Burst Address	A15 – A2	$\overline{A1}$	A0
3rd Burst Address	A15 – A2	$\overline{A1}$	$\overline{A0}$

NOTE: The burst wraps around to its initial state upon completion.

SYNCHRONOUS TRUTH TABLE (See Notes 1, 2, and 3)

$\overline{E}$	$\overline{ADSP}$	$\overline{ADSC}$	$\overline{ADV}$	$\overline{UW}$ or $\overline{LW}$	K	Address Used	Operation
H	L	X	X	X	L-H	N/A	Deselected
H	X	L	X	X	L-H	N/A	Deselected
L	L	X	X	X	L-H	External Address	Read Cycle, Begin Burst
L	H	L	X	L	L-H	External Address	Write Cycle, Begin Burst
L	H	L	X	H	L-H	External Address	Read Cycle, Begin Burst
X	H	H	L	L	L-H	Next Address	Write Cycle, Continue Burst
X	H	H	L	H	L-H	Next Address	Read Cycle, Continue Burst
X	H	H	H	L	L-H	Current Address	Write Cycle, Suspend Burst
X	H	H	H	H	L-H	Current Address	Read Cycle, Suspend Burst

NOTES:
1. X means Don't Care.
2. All inputs except $\overline{G}$ must meet setup and hold times for the low-to-high transition of clock (K).
3. Wait states are inserted by suspending burst.

ASYNCHRONOUS TRUTH TABLE (See Notes 1 and 2)

Operation	$\overline{G}$	I/O Status
Read	L	Data Out
Read	H	High-Z
Write	X	High-Z — Data In
Deselected	X	High-Z

NOTES:
1. X means Don't Care.
2. For a write operation following a read operation, $\overline{G}$ must be high before the input data required setup time and held high through the input data hold time.

ABSOLUTE MAXIMUM RATINGS (Voltages Referenced to V_{SS} = 0 V)

Rating	Symbol	Value	Unit
Power Supply Voltage	V_{CC}	− 0.5 to + 7.0	V
Voltage Relative to V_{SS} for Any Pin Except V_{CC}	V_{in}, V_{out}	− 0.5 to V_{CC} + 0.5	V
Output Current (per I/O)	I_{out}	± 30	mA
Power Dissipation	P_D	1.5	W
Temperature Under Bias	T_{bias}	− 10 to + 85	°C
Operating Temperature	T_A	0 to +70	°C
Storage Temperature	T_{stg}	− 55 to + 125	°C

NOTE: Permanent device damage may occur if ABSOLUTE MAXIMUM RATINGS are exceeded. Functional operation should be restricted to RECOMMENDED OPERATING CONDITIONS. Exposure to higher than recommended voltages for extended periods of time could affect device reliability.

This device contains circuitry to protect the inputs against damage due to high static voltages or electric fields; however, it is advised that normal precautions be taken to avoid application of any voltage higher than maximum rated voltages to this high-impedance circuit.

This BiCMOS memory circuit has been designed to meet the dc and ac specifications shown in the tables, after thermal equilibrium has been established.

This device contains circuitry that will ensure the output devices are in High-Z at power up.

DC OPERATING CONDITIONS AND CHARACTERISTICS

(V_{CC} = 5.0 V ± 5%, T_A = 0 to + 70°C, Unless Otherwise Noted)

RECOMMENDED OPERATING CONDITIONS (Voltages referenced to V_{SS} = 0 V)

Parameter	Symbol	Min	Max	Unit
Supply Voltage (Operating Voltage Range)	V_{CC}	4.75	5.25	V
Input High Voltage	V_{IH}	2.2	V_{CC} + 0.3**	V
Input Low Voltage	V_{IL}	– 0.5*	0.8	V

*V_{IL} (min) = – 0.5 V dc; V_{IL} (min) = – 2.0 V ac (pulse width ≤ 20.0 ns) for I ≤ 20.0 mA.
**V_{IH} (max) = V_{CC} + 0.3 V dc; V_{IH} (max) = V_{CC} + 2.0 V ac (pulse width ≤ 20.0 ns) for I ≤ 20.0 mA.

DC CHARACTERISTICS AND SUPPLY CURRENTS

Parameter	Symbol	Min	Max	Unit
Input Leakage Current (All Inputs, V_{in} = 0 to V_{CC})	$I_{lkg(I)}$	—	± 1.0	µA
Output Leakage Current ($\overline{G}$ = V_{IH})	$I_{lkg(O)}$	—	± 1.0	µA
AC Supply Current ($\overline{G}$ = V_{IH}, $\overline{E}$ = V_{IL}, I_{out} = 0 mA, All Inputs = V_{IL} or V_{IH}, V_{IL} = 0.0 V and V_{IH} ≥ 3.0 V, Cycle Time ≥ t_{KHKH} min) I_{CCA9} I_{CCA12} I_{CCA18}		—	 275 250 225	mA
AC Standby Current ($\overline{E}$ = V_{IH}, I_{out} = 0 mA, All Inputs = V_{IL} and V_{IH}, V_{IL} = 0.0 V and V_{IH} ≥ 3.0 V, Cycle Time ≥ t_{KHKH} min)	I_{SB1}	—	75	mA
Output Low Voltage (I_{OL} = + 8.0 mA)	V_{OL}	—	0.4	V
Output High Voltage (I_{OH} = – 4.0 mA)	V_{OH}	2.4	3.3	V

NOTE: Good decoupling of the local power supply should always be used. DC characteristics are guaranteed for all possible i486 and Pentium bus cycles.

CAPACITANCE (f = 1.0 MHz, dV = 3.0 V, T_A = 25°C, Periodically Sampled Rather Than 100% Tested)

Parameter	Symbol	Typ	Max	Unit
Input Capacitance (All Pins Except DQ0 – DQ17)	C_{in}	4	5	pF
Input/Output Capacitance (DQ0 – DQ17)	$C_{I/O}$	6	8	pF

AC OPERATING CONDITIONS AND CHARACTERISTICS

(V_{CC} = 5.0 V ± 5%, T_A = 0 to + 70°C, Unless Otherwise Noted)

Input Timing Measurement Reference Level ..... 1.5 V
Input Pulse Levels ..... 0 to 3.0 V
Input Rise/Fall Time ..... 3 ns

Output Timing Reference Level ..... 1.5 V
Output Load ..... See Figure 1A Unless Otherwise Noted

READ/WRITE CYCLE TIMING (See Notes 1, 2, and 3) ($\overline{W}$ refers to either or both byte write enables)

Parameter	Symbol		MCM67B618-9		MCM67B618-12		MCM67B618-18		Unit	Notes
	Standard	Alternate	Min	Max	Min	Max	Min	Max		
Cycle Time	t_{KHKH}	t_{CYC}	15	—	20	—	30	—	ns	
Clock Access Time	t_{KHQV}	t_{CD}	—	9	—	12	—	18	ns	4
Output Enable to Output Valid	t_{GLQV}	t_{OE}	—	5	—	6	—	7	ns	
Clock High to Output Active	t_{KHQX1}	t_{DC1}	6	—	6	—	6	—	ns	
Clock High to Output Change	t_{KHQX2}	t_{DC2}	3	—	3	—	3	—	ns	
Output Enable to Output Active	t_{GLQX}	t_{OLZ}	0	—	0	—	0	—	ns	
Output Disable to Q High-Z	t_{GHQZ}	t_{OHZ}	2	6	2	7	2	7	ns	5
Clock High to Q High-Z	t_{KHQZ}	t_{CZ}	—	6	—	6	—	6	ns	
Clock High Pulse Width	t_{KHKL}	t_{CH}	5	—	6	—	7	—	ns	
Clock Low Pulse Width	t_{KLKH}	t_{CL}	5	—	6	—	7	—	ns	
Setup Times: Address	t_{AVKH}	t_{AS}	2.5	—	2.5	—	3.0	—	ns	6
Address Status	t_{ADSVKH}	t_{SS}								
Data In	t_{DVKH}	t_{DS}								
Write	t_{WVKH}	t_{WS}								
Address Advance	t_{ADVVKH}									
Chip Enable	t_{EVKH}									
Hold Times: Address	t_{KHAX}	t_{AH}	0.5	—	0.5	—	0.5	—	ns	6
Address Status	t_{KHADSX}	t_{SH}								
Data In	t_{KHDX}	t_{DH}								
Write	t_{KHWX}	t_{WH}								
Address Advance	t_{KHADVX}									
Chip Enable	t_{KHEX}									

NOTES:
1. A read cycle is defined by $\overline{UW}$ and $\overline{LW}$ high or $\overline{ADSP}$ low for the setup and hold times. A write cycle is defined by $\overline{LW}$ or $\overline{UW}$ low and $\overline{ADSP}$ high for the setup and hold times.
2. All read and write cycle timings are referenced from K or $\overline{G}$.
3. $\overline{G}$ is a don't care when $\overline{UW}$ or $\overline{LW}$ is sampled low.
4. Maximum access times are guaranteed for all possible i486 external bus cycles.
5. Transition is measured ± 500 mV from steady-state voltage with load of Figure 1B. This parameter is sampled rather than 100% tested. At any given voltage and temperature, t_{KHQZ} max is less than t_{KHQZ1} min for a given device and from device to device.
6. This is a synchronous device. All addresses must meet the specified setup and hold times for ***ALL*** rising edges of K whenever $\overline{ADSP}$ or $\overline{ADSC}$ is low, and the chip is selected. All other synchronous inputs must meet the specified setup and hold times for ***ALL*** rising edges of K when the chip is enabled.Chip enable must be valid at each rising edge of clock for the device (when $\overline{ADSP}$ or $\overline{ADSC}$ is low) to remain enabled.

AC TEST LOADS

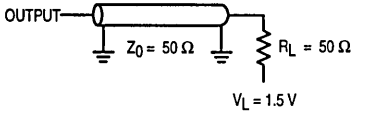


Figure 1A

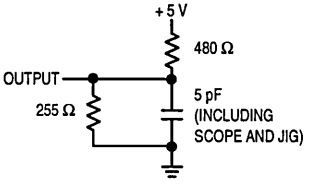
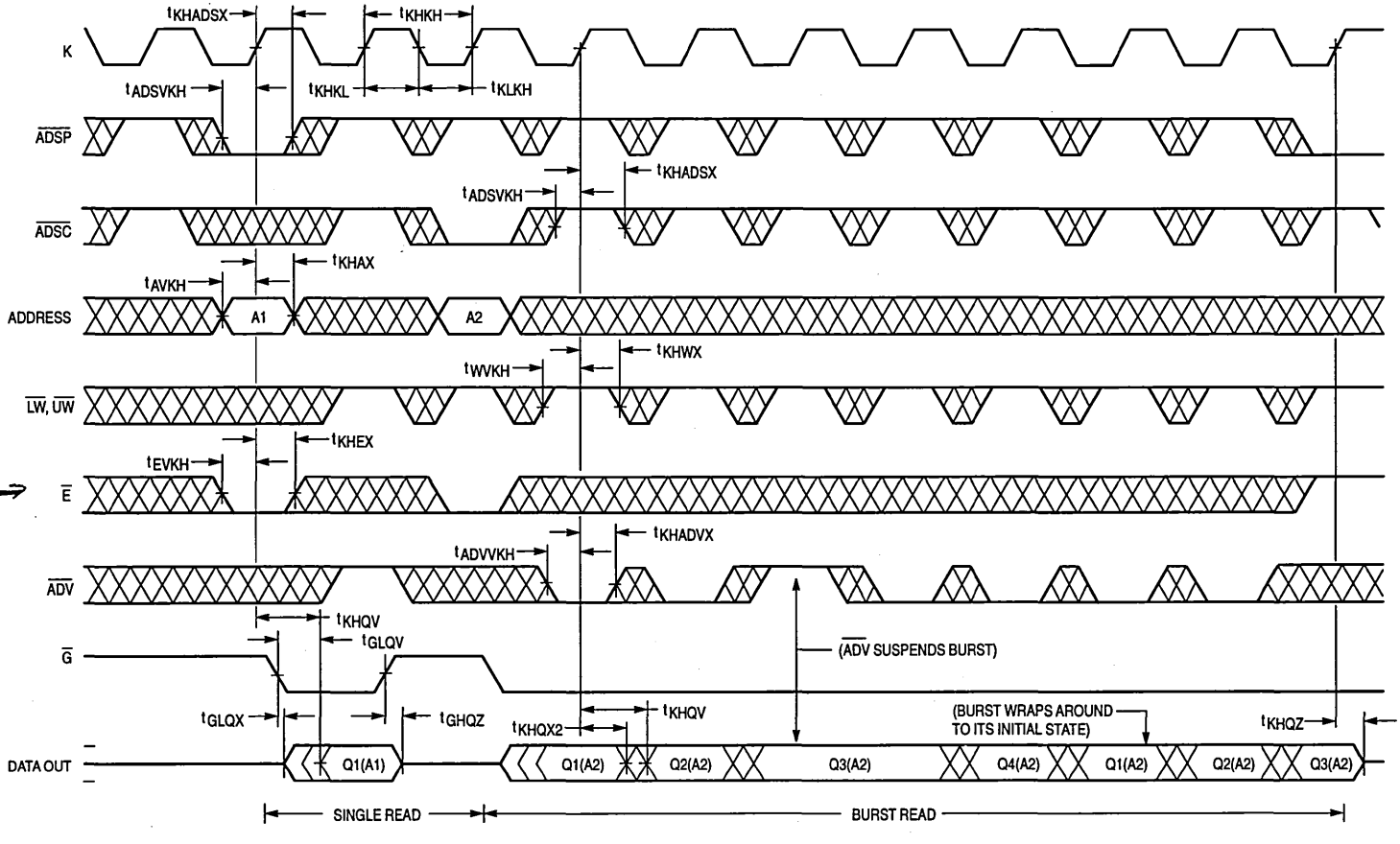


Figure 1B

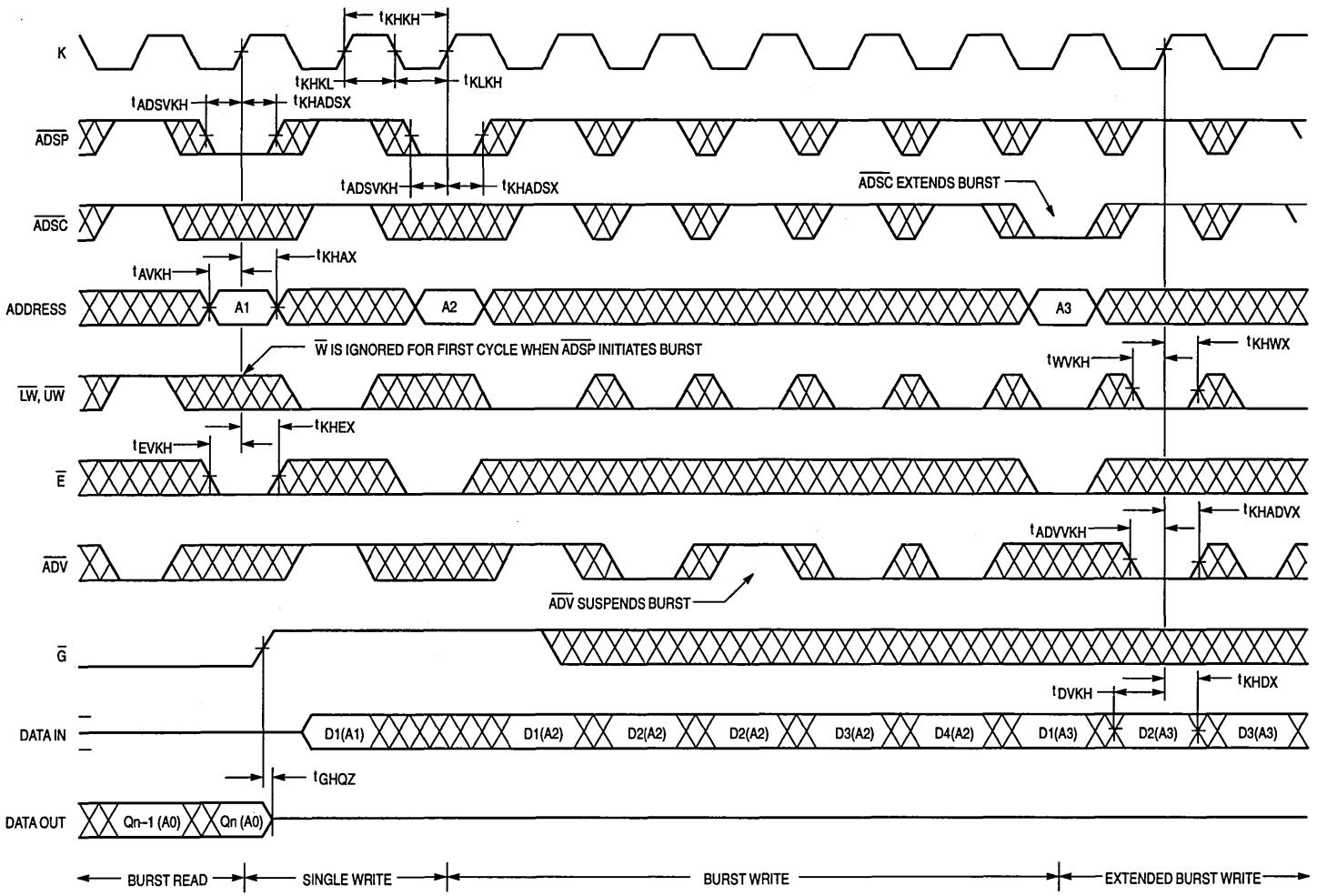
NOTE: For information on output I-V characteristics, see Chapter 8, Section 1.

READ CYCLES

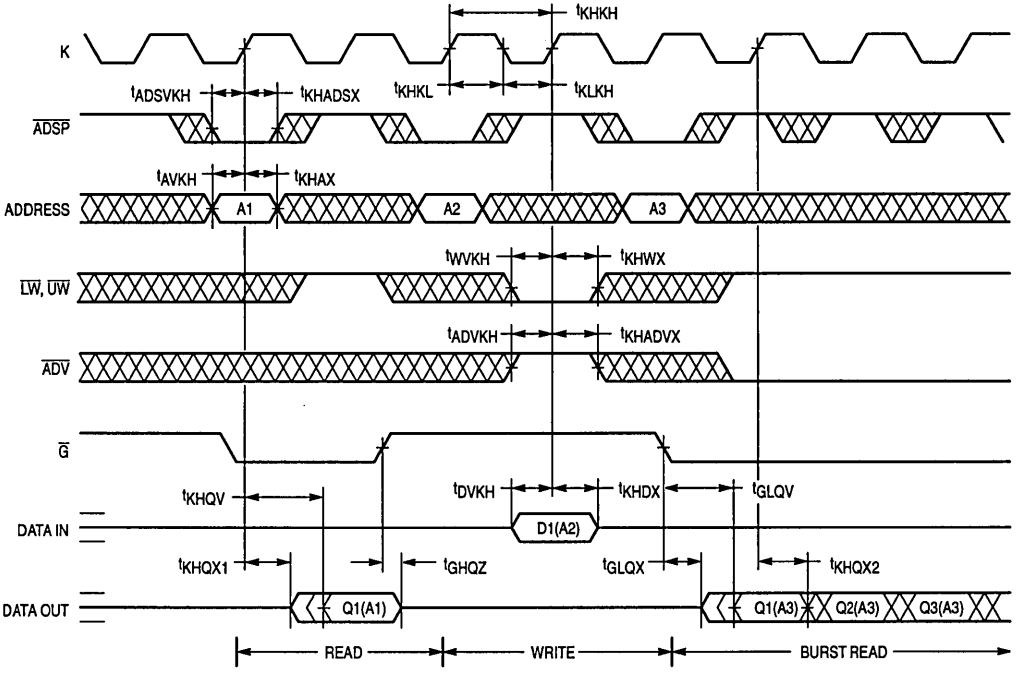


NOTE: Q1(A2) represents the first output data from the base address A2; Q2(A2) represents the next output data in the burst sequence with A2 as the base address.

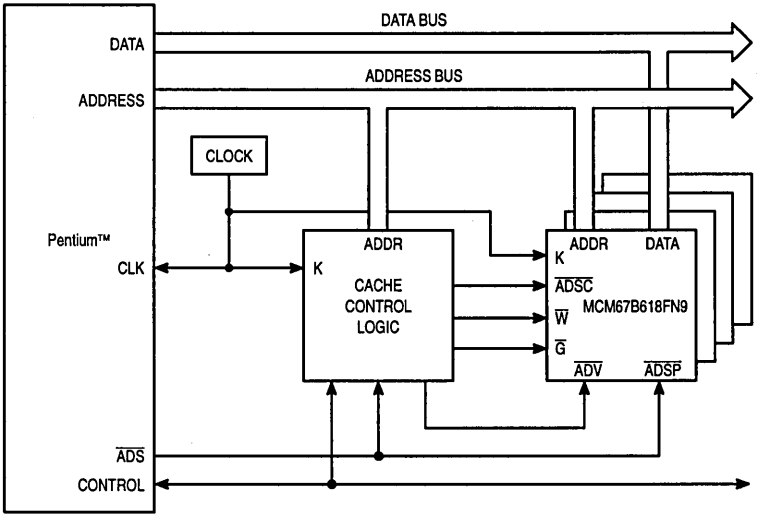
WRITE CYCLES



COMBINATION READ/WRITE CYCLE



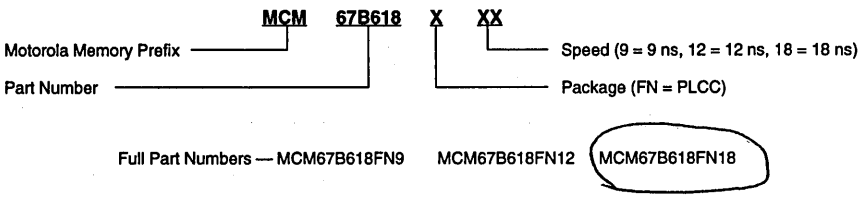
APPLICATION EXAMPLE



512K Byte Burstable, Secondary Cache
Using Four MCM67B618FN9s with a 66 MHz Pentium

Figure 2

ORDERING INFORMATION
(Order by Full Part Number)



Full Part Numbers — MCM67B618FN9 MCM67B618FN12 MCM67B618FN18